Power MOSFETS

DATASHEET

LM40060NAQ8A

N-Channel

Enhancement Mode MOSFET

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Quality Management Systems

ISO 9001:2015 Certificate

LM40060NAQ8A

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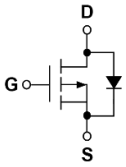
Pin Description

SOP-8L	Symbol
	

Product Summary

Symbol	N-Channel	Unit
V_{DSS}	40	V
$R_{DS(ON)-Max}$	5.3	mΩ
ID	13.8	A

Feature

- Fast switching speed
- Reliable and Rugged
- ROHS Compliant & Halogen-Free
- 100% UIS and Rg Tested

Applications

- Portable Equipment
- Battery Powered System

Ordering Information

Orderable Part Number	Package Type	Form	Shipping	Marking
LM40060NAQ8A	SOP-8L	Tape & Reel	3000 / Tape & Reel	40060 □□□□□□

Absolute Maximum Ratings (T_J=25°C Unless Otherwise Noted)

Symbol	Parameter		N-Channel	Unit
V_{DSS}	Drain-Source Voltage		40	V
V_{GSS}	Gate-Source Voltage		±20	
T_J	Maximum Junction Temperature		150	°C
T_{STG}	Storage Temperature Range		-55 to 150	°C
I_S	Diode Continuous Forward Current	T_A=25°C	0.6	A
I_{DM}①	Pulse Drain Current Tested	T_A=25°C	35	A
I_D	Continuous Drain Current	T_A=25°C	13.8	A
		T_A=100°C	8.7	
P_D	Maximum Power Dissipation	T_A=25°C	1.5	W
		T_A=100°C	0.9	
I_{AS}②	Avalanche Current, Single pulse	L=0.1mH	16	A
		L=0.5mH	8	
E_{AS}②	Avalanche Energy, Single pulse	L=0.1mH	13	mJ
		L=0.5mH	16	

Thermal Characteristics

Symbol	Parameter		Rating	Unit
$R_{\theta JA}$③	Thermal Resistance-Junction to Ambient	t≦10s	85	°C/W
		Steady State	43	°C/W

Note ① : Max. current is limited by junction temperature

Note ② : UIS tested and pulse width are limited by maximum junction temperature 150°C

Note ③ : Surface Mounted on 1in^2 FR-4 board with 1oz.

N-Channel Electrical Characteristics (T_J=25°C Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Electrical Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_{DS}=250uA	40	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=32V, V_{GS}=0V	-	-	1	uA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_{DS}=250uA	1	1.5	2	V
I_{GSS}	Gate Leakage Current	V_{GS}=±20V, V_{DS}=0V	-	-	±100	nA
$R_{DS(ON)}$④	Drain-Source On-state Resistance	V_{GS}=10V, I_{DS}=20A	-	4.4	5.3	mΩ
		V_{GS}=4.5V, I_{DS}=10A	-	6.2	8	
gfs	Forward Transconductance	V_{DS}=5V, I_{DS}=10A	-	12	-	S
Dynamic Characteristics ⑤						
R_G	Gate Resistance	V_{GS}=0V,V_{DS}=0V, Freq.=1MHz	-	2.3	-	Ω
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=20V, Freq.=1MHz	-	927	-	pF
C_{oss}	Output Capacitance		-	366	-	
C_{rss}	Reverse Transfer Capacitance		-	58	-	
$td_{(ON)}$	Turn-on Delay Time	V_{GS}=10V,V_{DS}=25V, I_D=1A,R_{GEN}=1Ω	-	8.5	-	nS
t_r	Turn-on Rise Time		-	5.5	-	
$t_{d(OFF)}$	Turn-off Delay Time		-	26.9	-	
t_f	Turn-off Fall Time		-	40.5	-	
Q_g	Total Gate Charge	V_{GS}=4.5V,V_{DS}=20V I_D=20A	-	11.6	-	nC
Q_g	Total Gate Charge	V_{GS}=10V,V_{DS}=20V, I_D=20A	-	21.7	-	
Q_{gs}	Gate-Source Charge		-	3.2	-	
Q_{gd}	Gate-Drain Charge		-	6	-	
Source-Drain Characteristics						
V_{SD}④	Diode Forward Voltage	I_{SD}=10A, V_{GS}=0V	-	0.75	1.1	V
t_{rr}	Reverse Recovery Time	I_F=10A, V_R=20V dI$_F$/dt=100A/μs	-	29.5	-	nS
Q_{rr}	Reverse Recovery Charge		-	14.1	-	nC

Note ④：Pulse test (pulse width≤300us, duty cycle≤2%).
Note ⑤：Guaranteed by design, not subject to production testing.

N-Channel Typical Characteristics

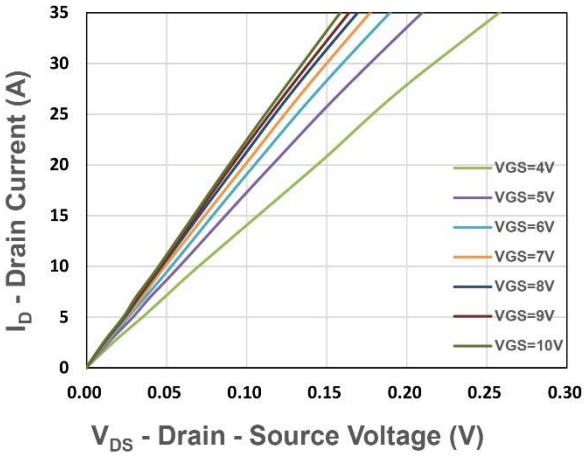


Figure 1. Output Characteristics

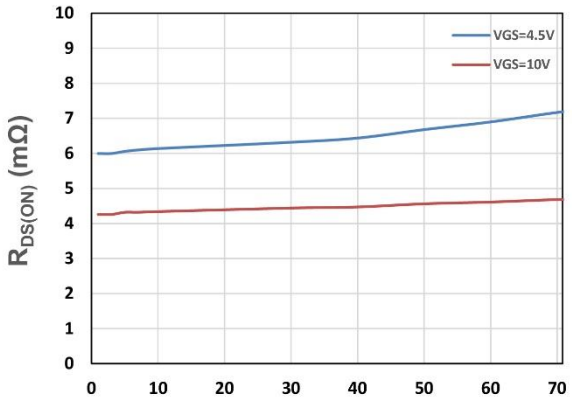


Figure 2. On-Resistance vs. ID

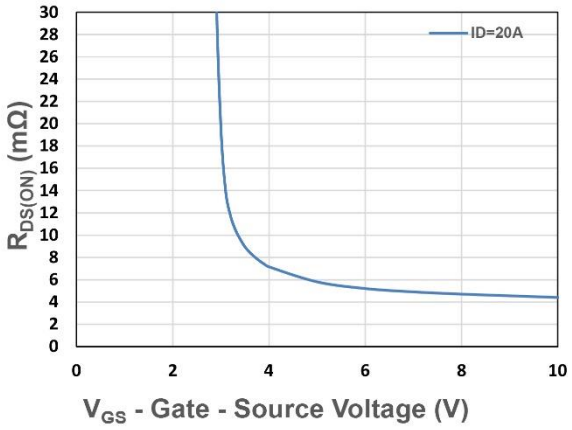


Figure 3. On-Resistance vs. VGS

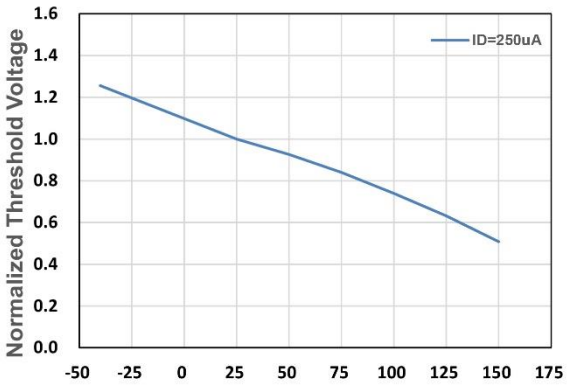


Figure 4. Gate Threshold Voltage

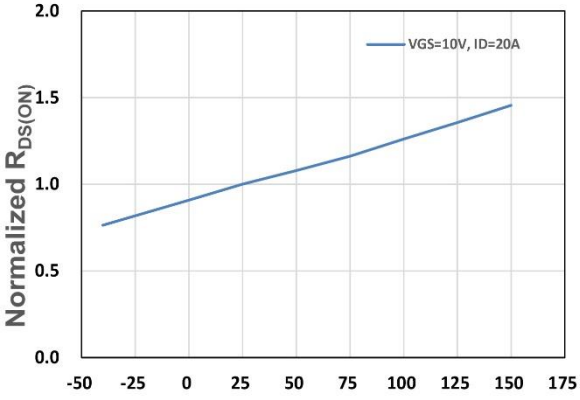


Figure 5. Drain-Source On Resistance

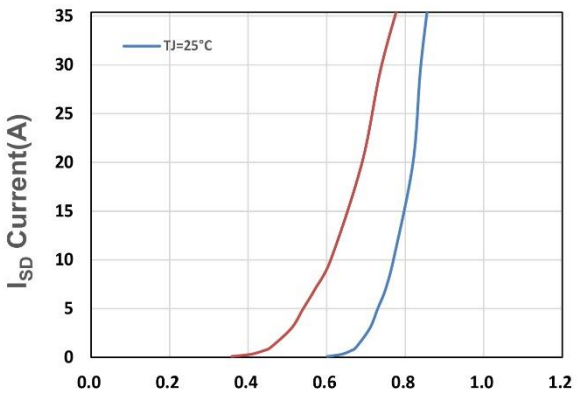


Figure 6. Source-Drain Diode Forward

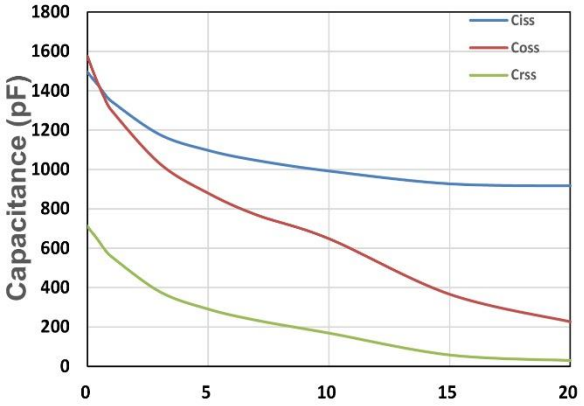


Figure 7. Capacitance

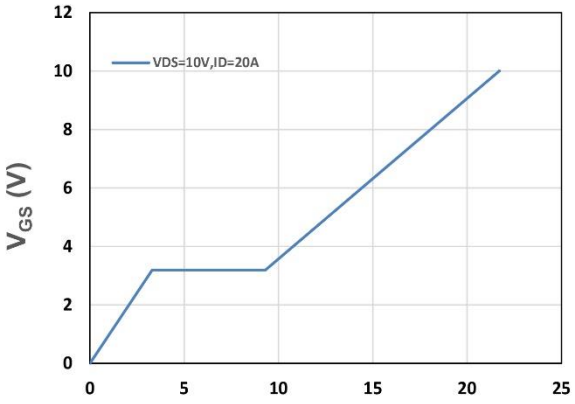


Figure 8. Gate Charge Characteristics

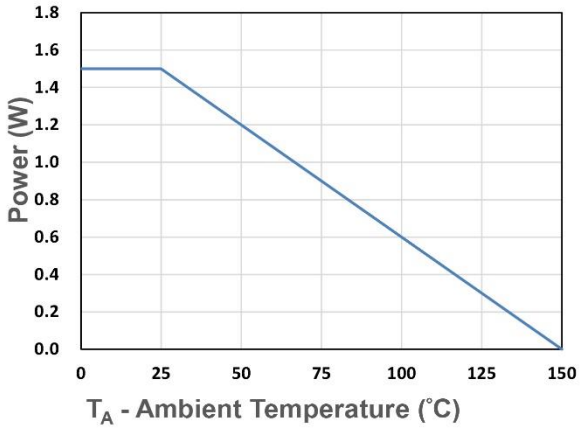


Figure 9. Power Dissipation

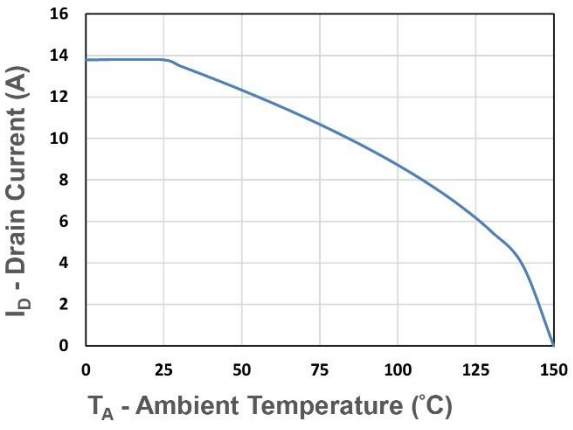


Figure 10. Drain Current

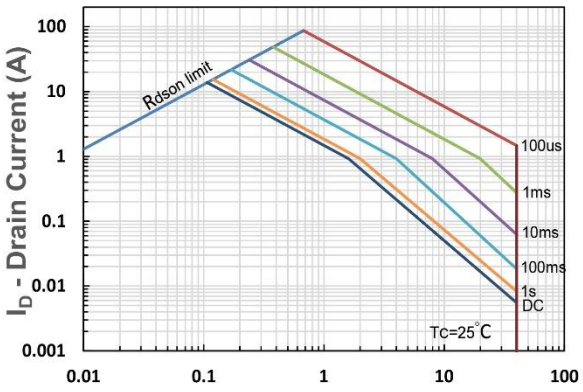


Figure 11. Safe Operating Area

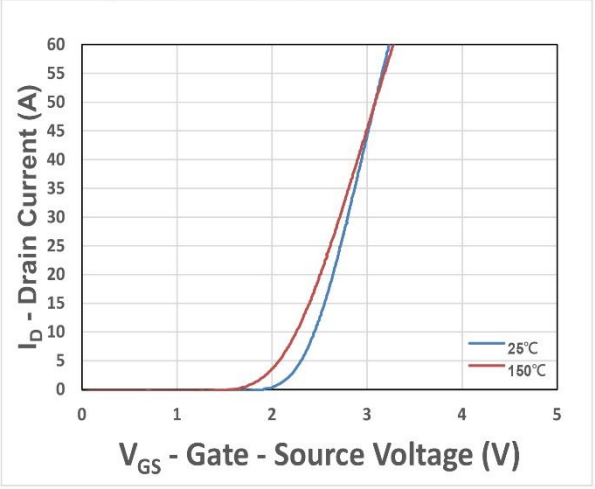


Figure 12. Transfer Characteristics

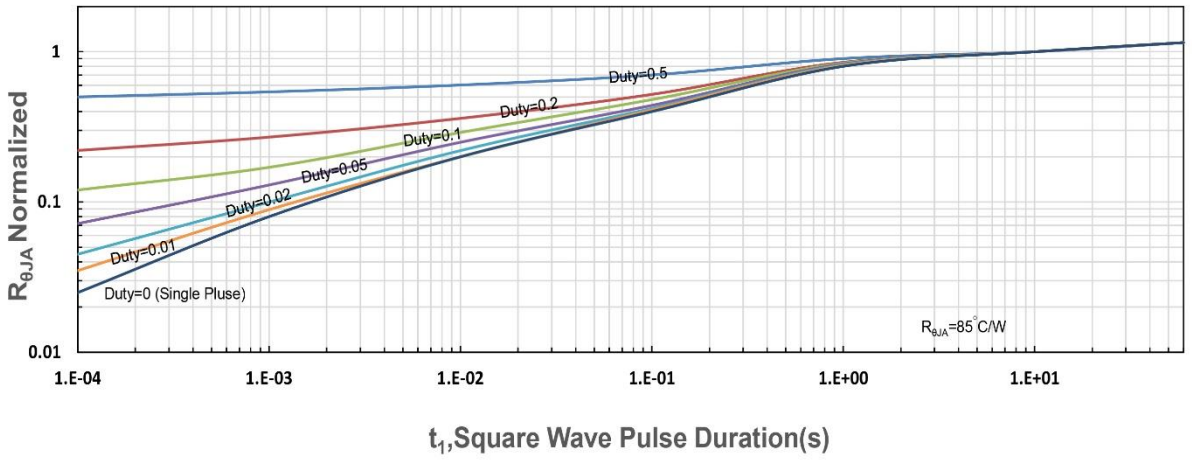


Figure 13. RθJA Transient Thermal Impedance